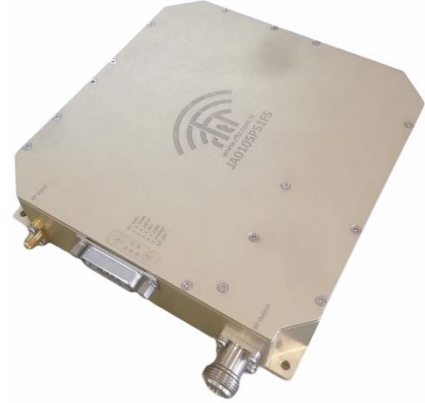


JA01000500P51FS; 100-500 MHz 150W

- Solid-state Class AB design
- Rugged MOS Transistors
- High reliability and ruggedness
- Ultra Broadband
- Temperature and Current Monitorings



ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

Frequency:	100-500 MHz
Output Power:	150 W min. CW
Nominal Gain:	51 dB
Gain Flatness:	± 2.0 dB
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1 for 1min.
DC Supply Voltage:	28 V
DC Current:	12.5 A Avg
ON/OFF Switching Time	<6 usec.
Operating Case Temp.:	-40 °C to 85 °C
Storage Temperature:	-40 °C to 85 °C
Shock:	MIL-STD-810F, 516.5
Vibration:	MIL-STD-810F, 514.5

INTERFACES

RF Input:	SMA Female
RF Output:	N Female
COMBO 7W2:	A1) GND A2) 28 V 1) Temperature 2) Current 3) Reverse Power 4) Forward Power 5) Enable (Active Low)

MECHANICAL SPECIFICATIONS

Size (mm) :	150 x 145 x 34
Weight :	800 gr.
Plating :	Yellow Chromate

